

FIG. 2 (a)

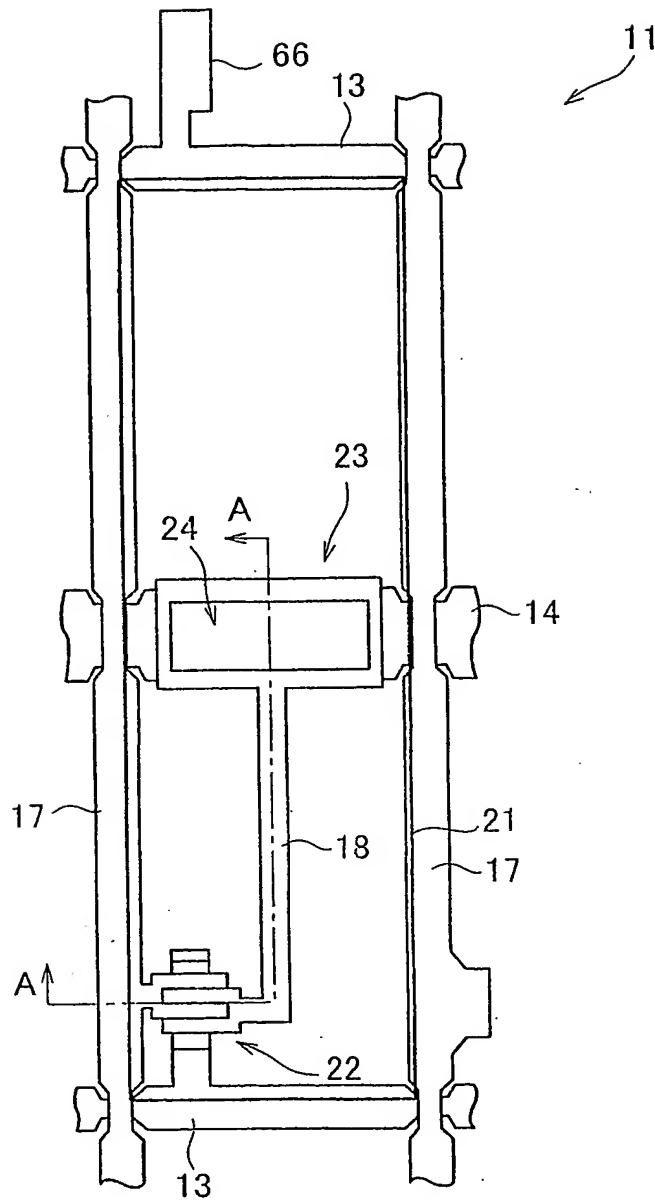
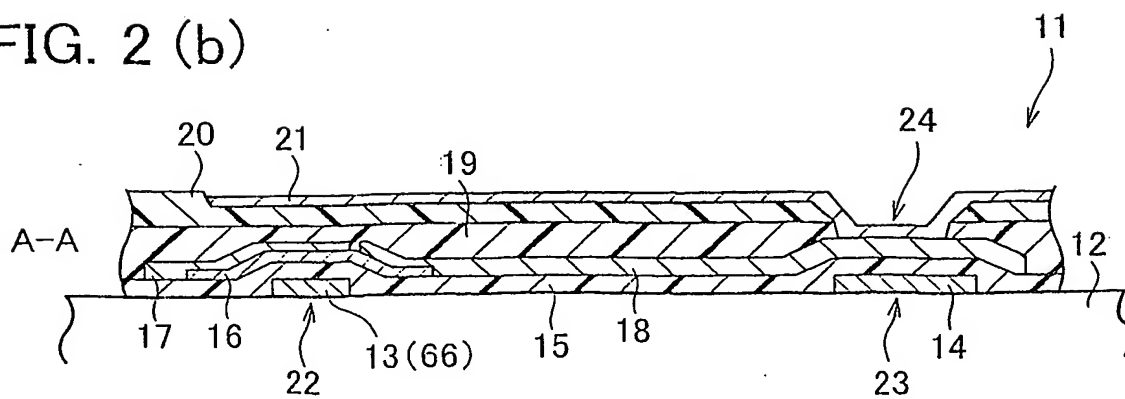


FIG. 2 (b)



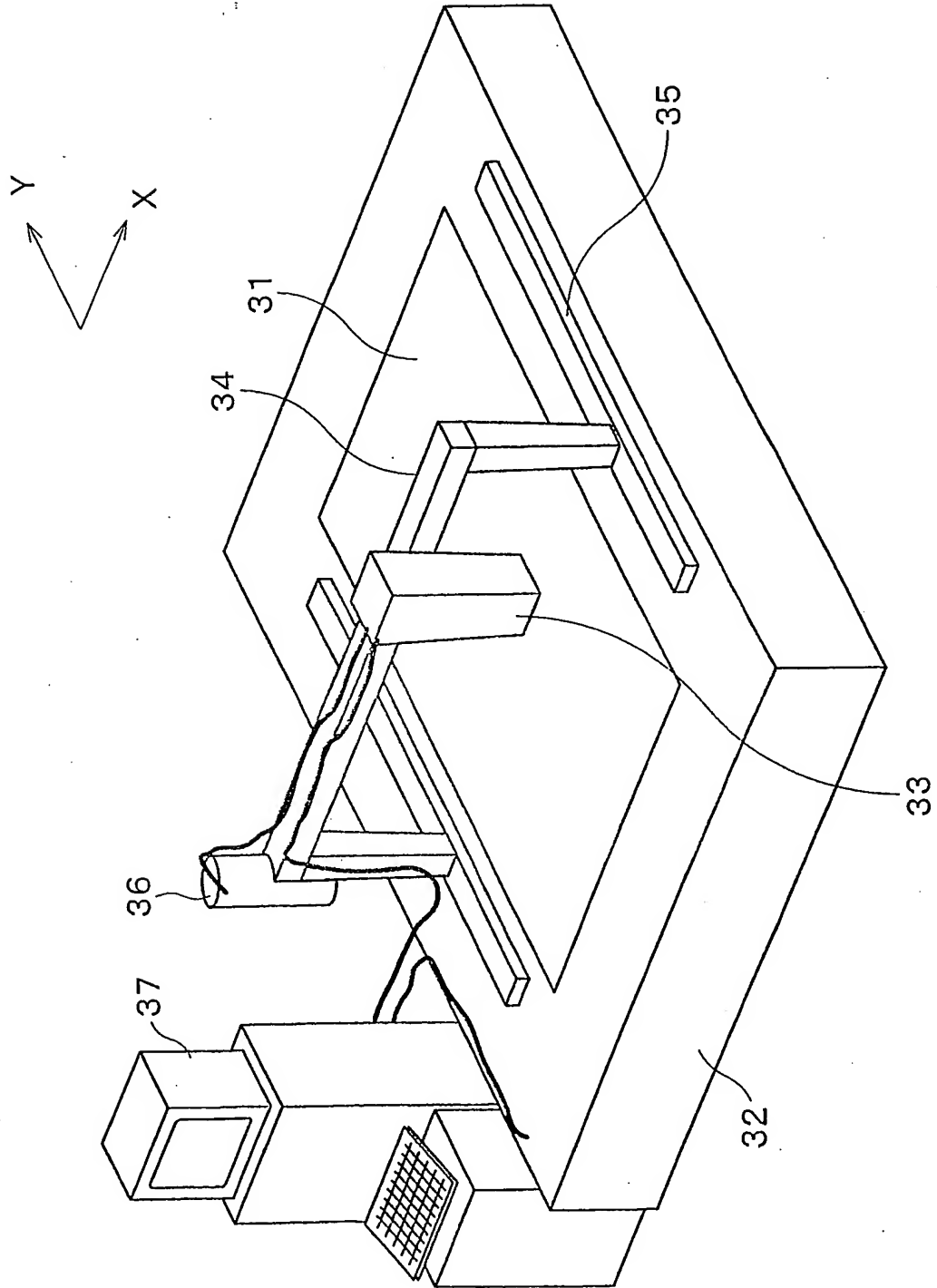


FIG. 3

FIG. 4

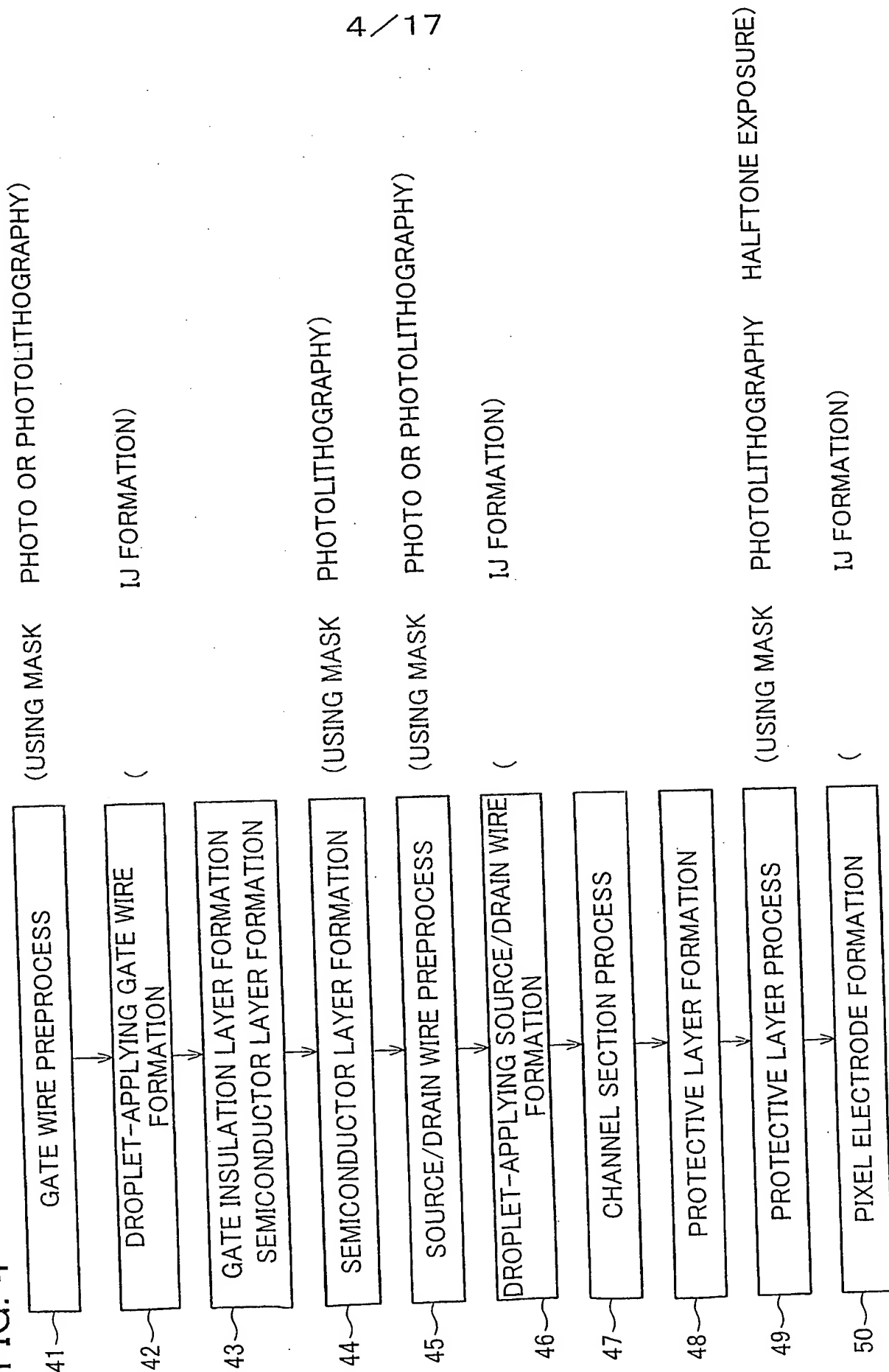


FIG. 5 (a)

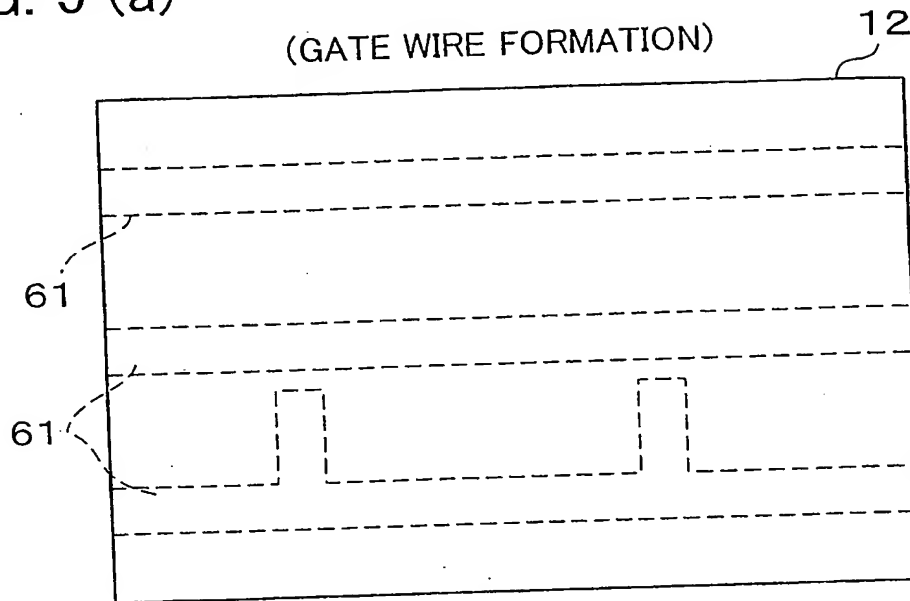


FIG. 5 (b)

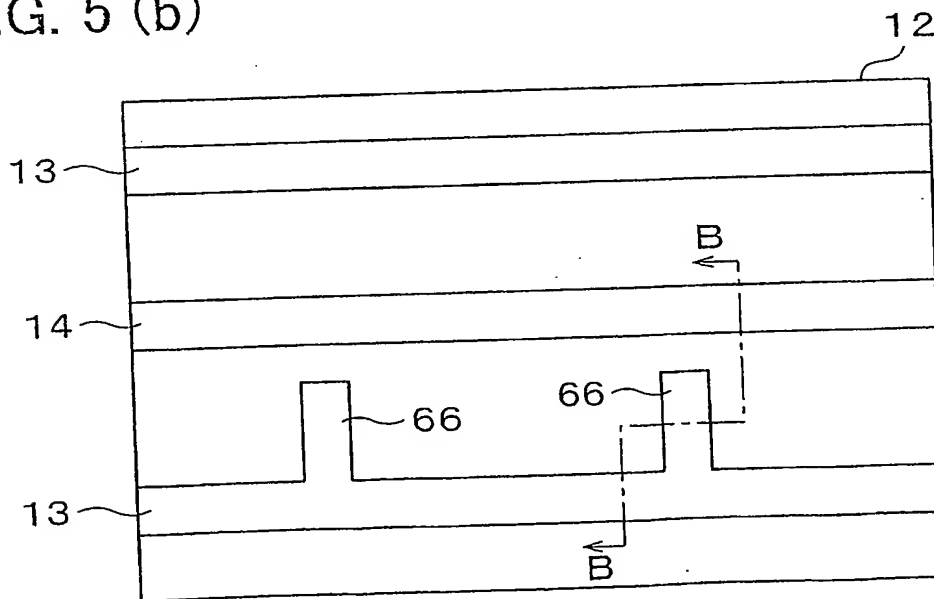
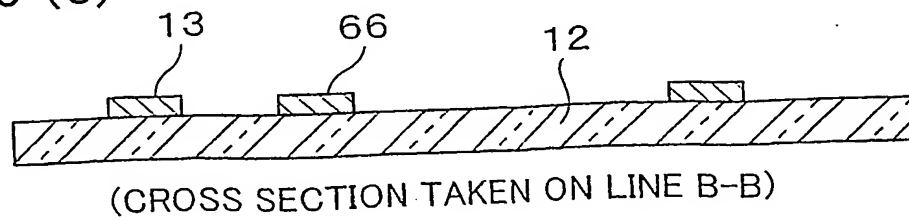


FIG. 5 (c)



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FIG. 6 (a) (SEMICONDUCTOR LAYER FORMATION)

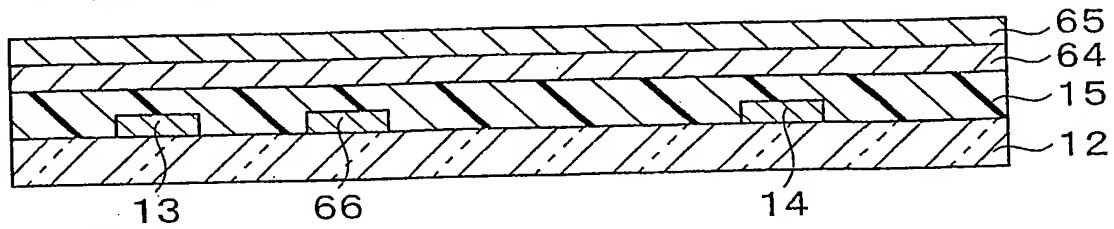


FIG. 6 (b)

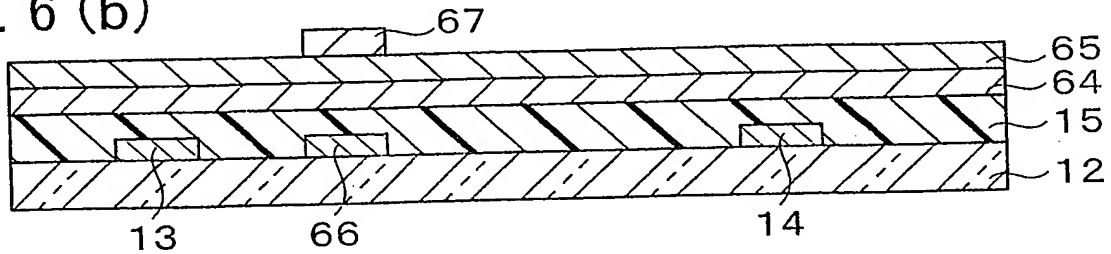


FIG. 6 (c)

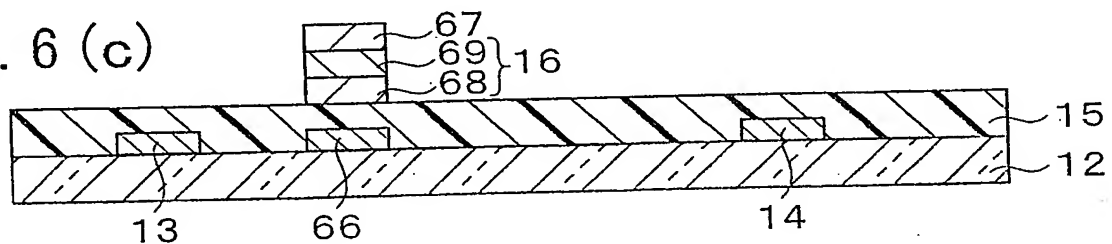


FIG. 6 (d)

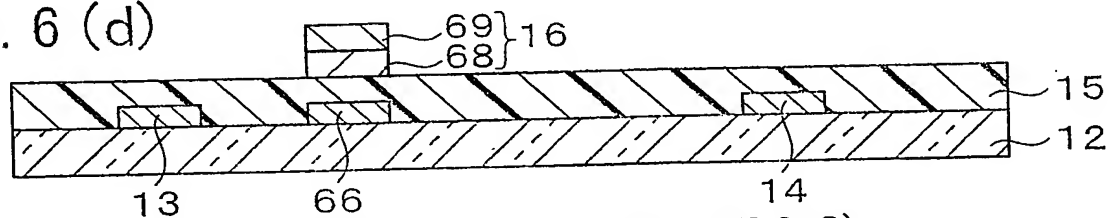


FIG. 6 (e) (CROSS SECTION TAKEN ON LINE C-C)

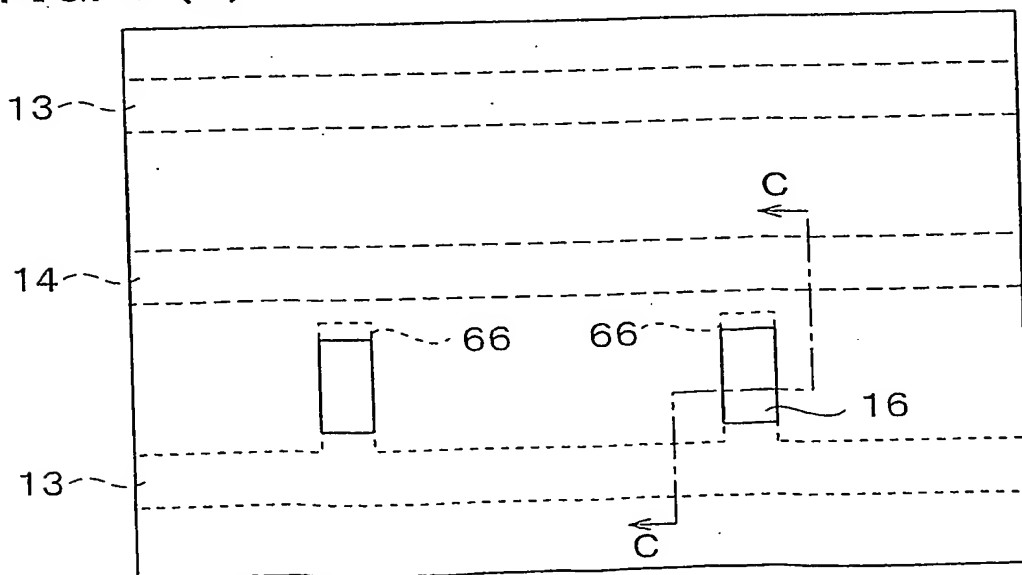


FIG. 7

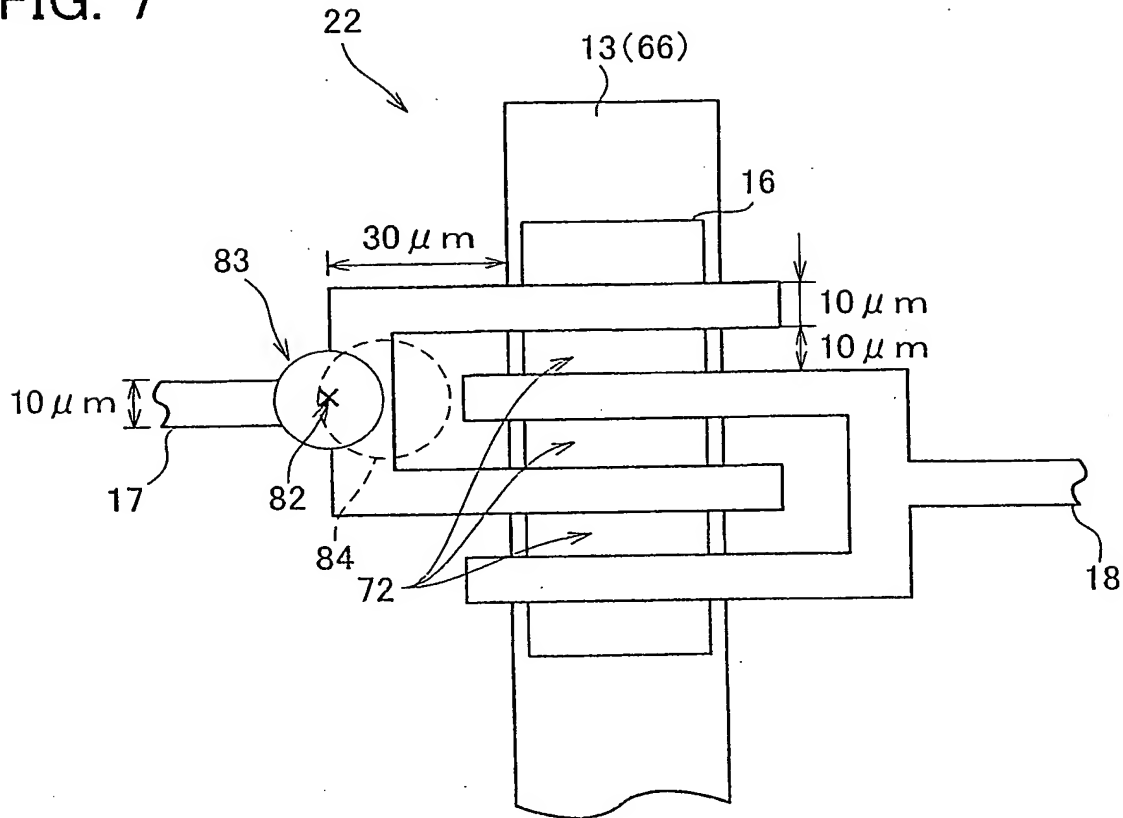


FIG. 8

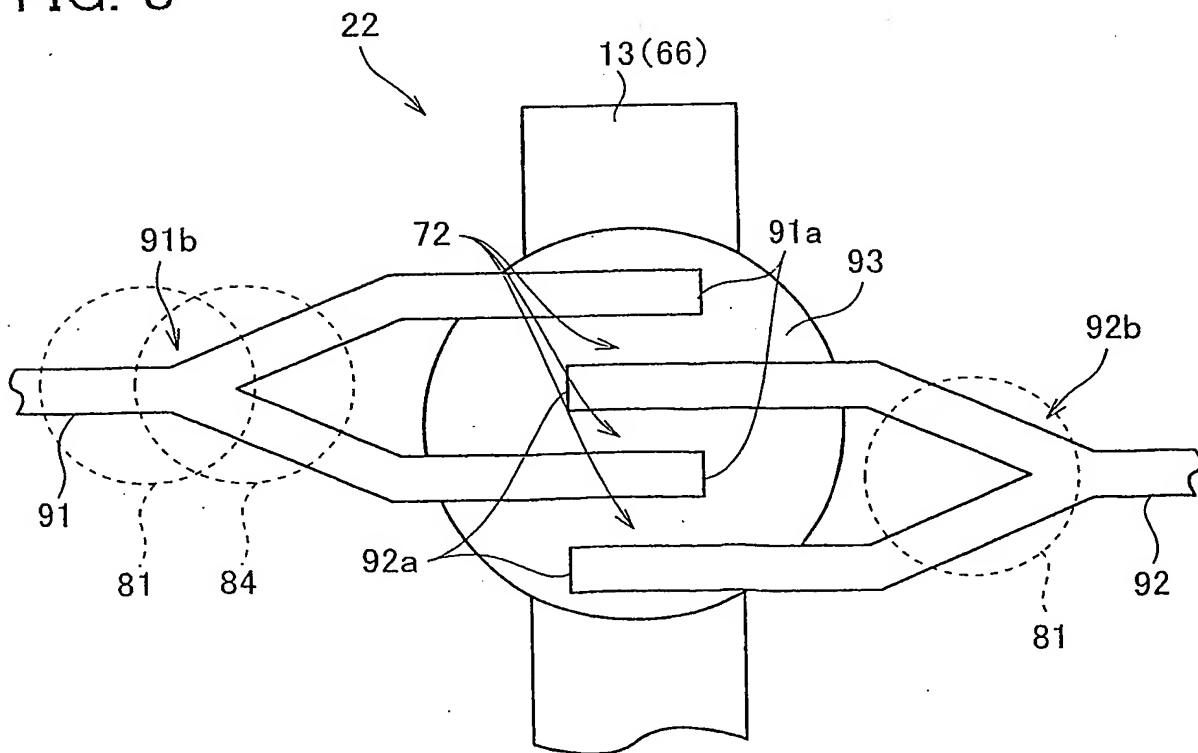


FIG. 9 (a) (SEMICONDUCTOR LAYER FORMATION)

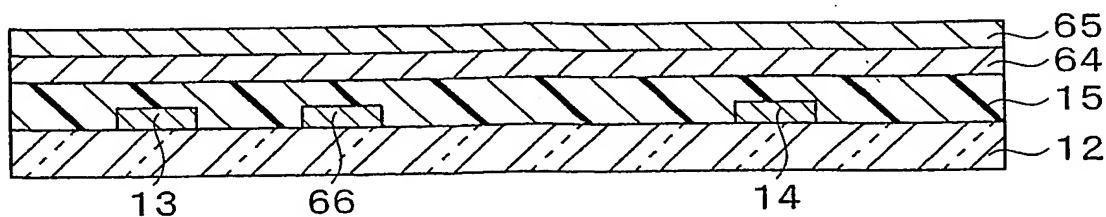


FIG. 9 (b)

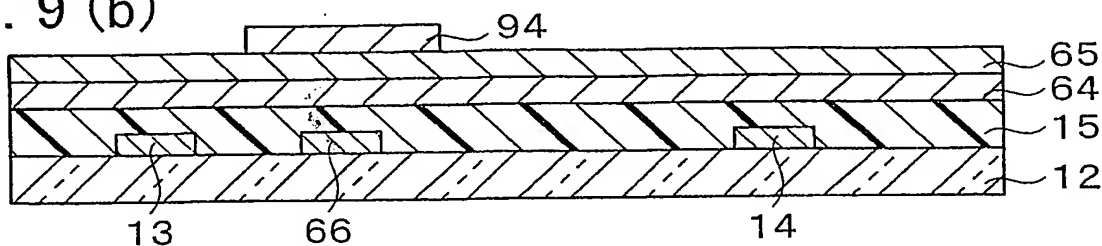


FIG. 9 (c)

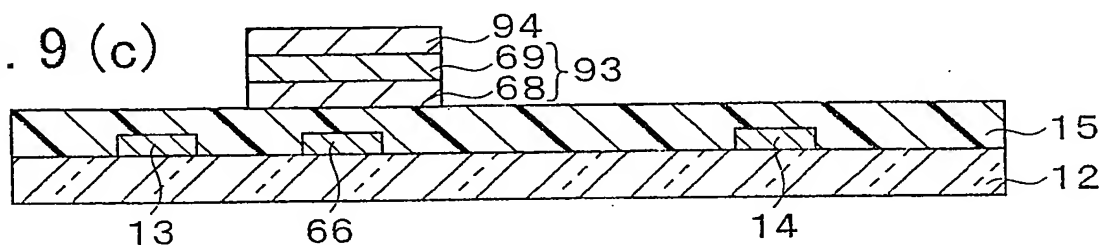


FIG. 9 (d)

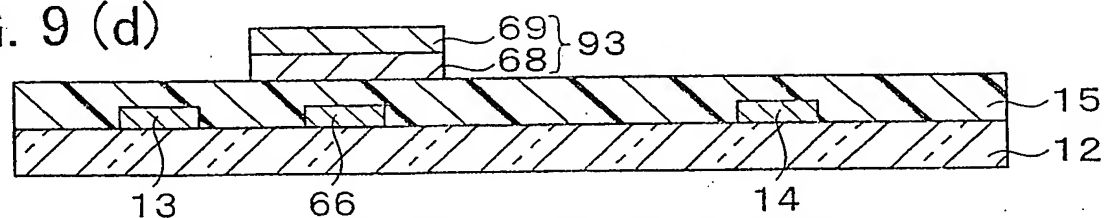


FIG. 9 (e) (CROSS SECTION TAKEN ON LINE C-C)

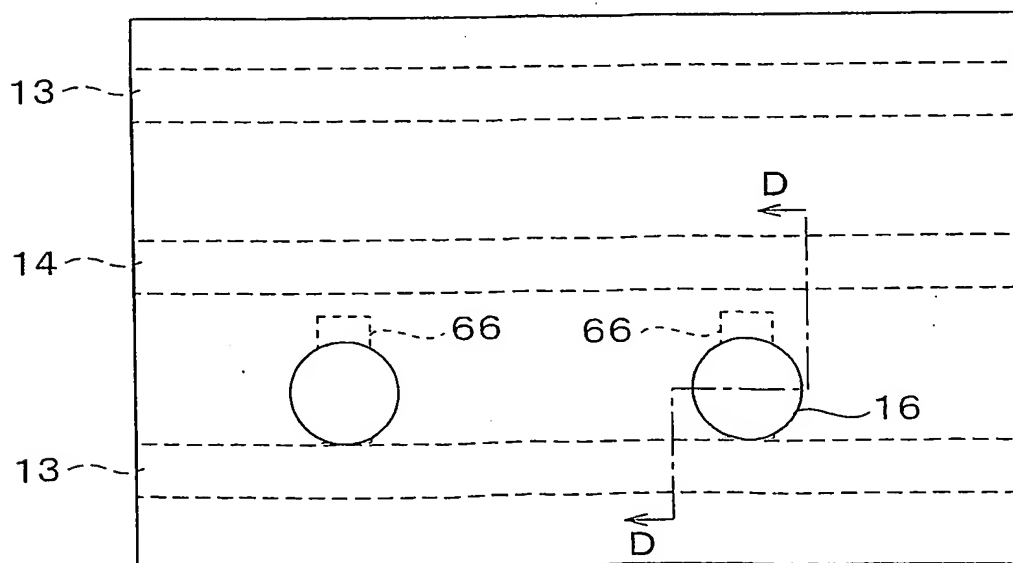




FIG. 10 (a)

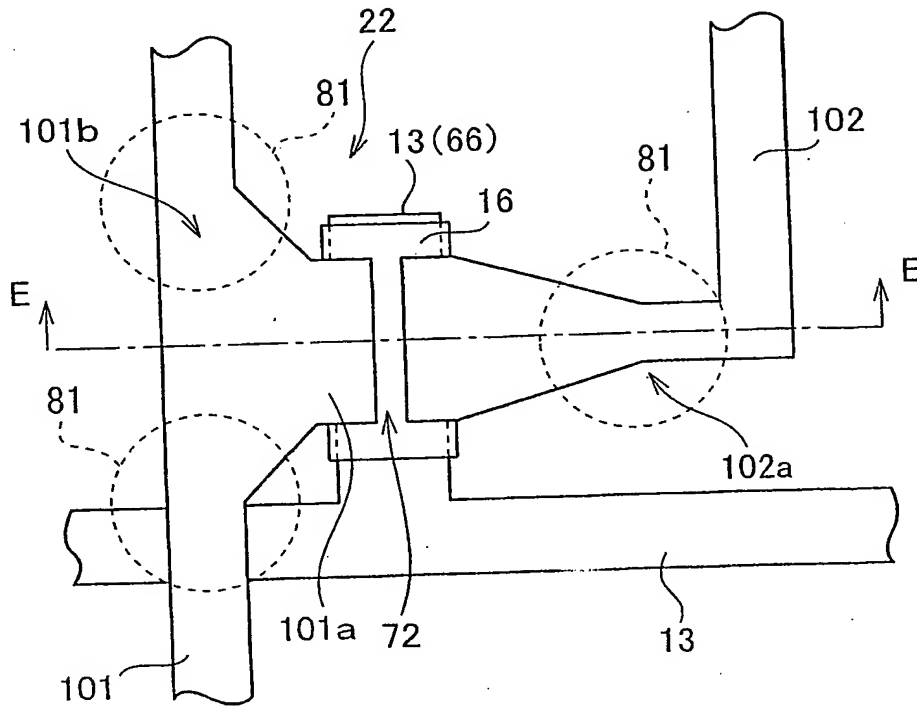
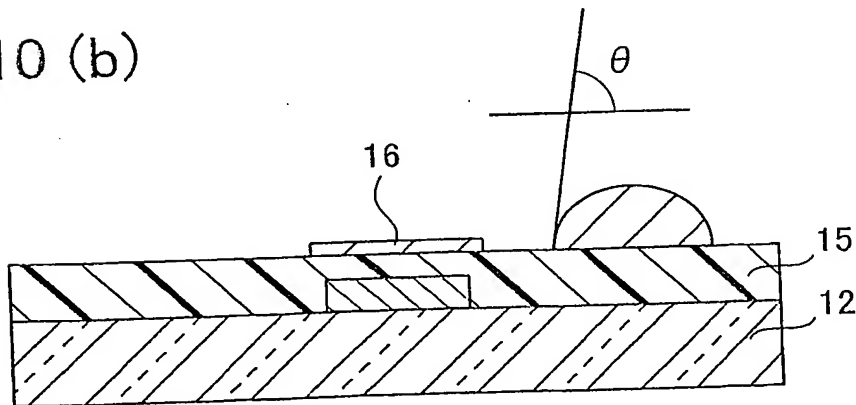


FIG. 10 (b)



(CROSS SECTION TAKEN ON LINE E-E)

FIG. 11

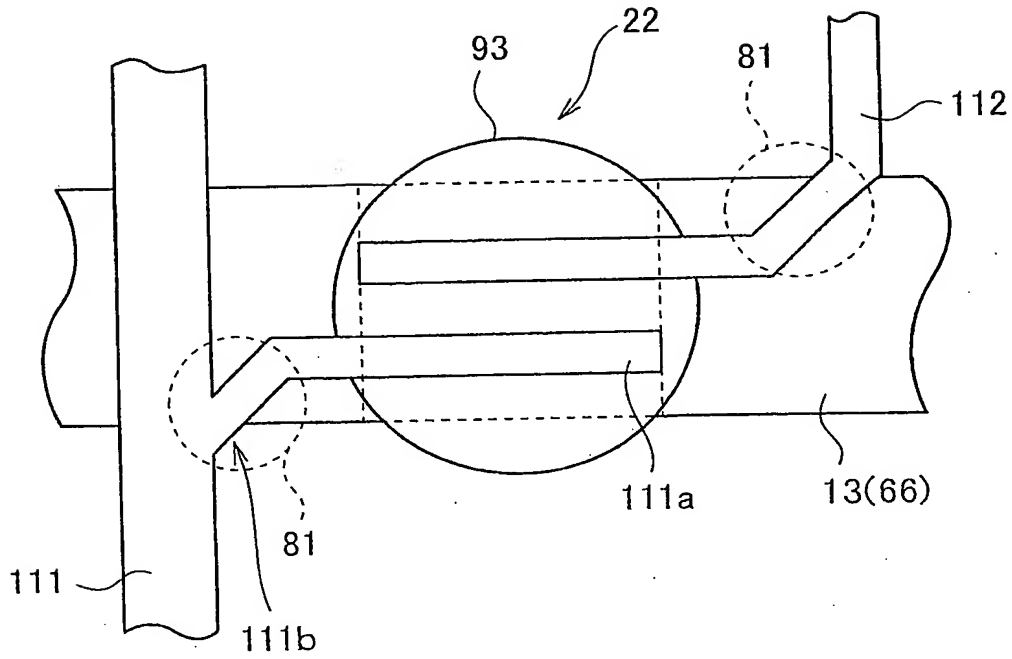


FIG. 12 (a)

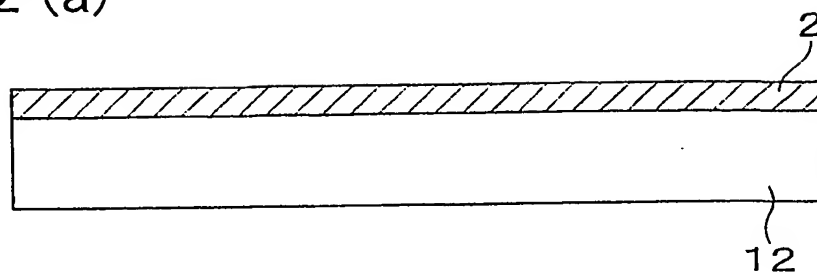


FIG. 12 (b)

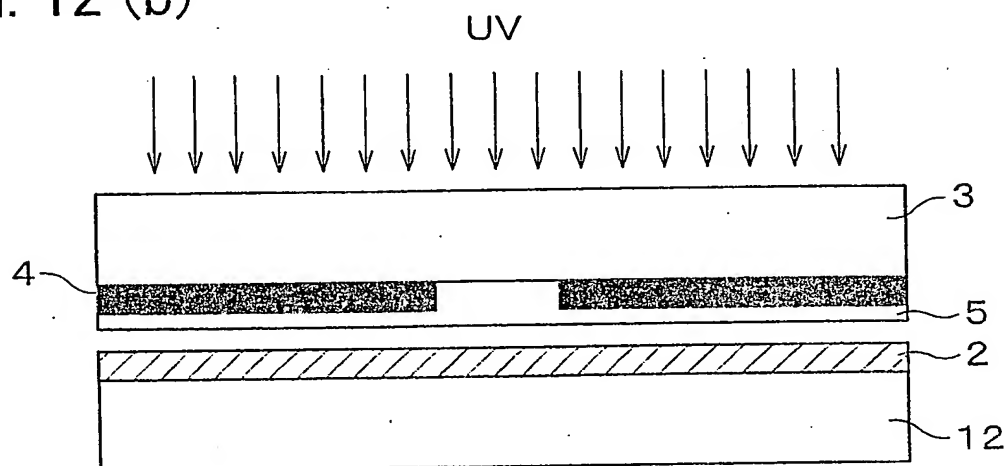


FIG. 12 (c)

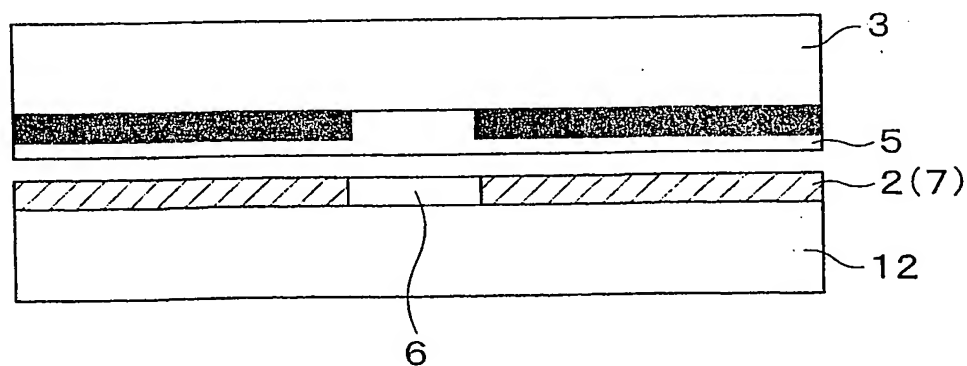


FIG. 12 (d)

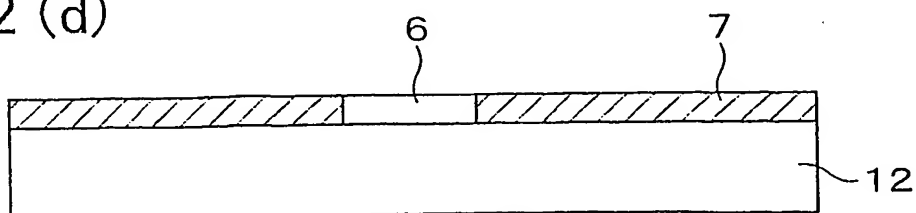
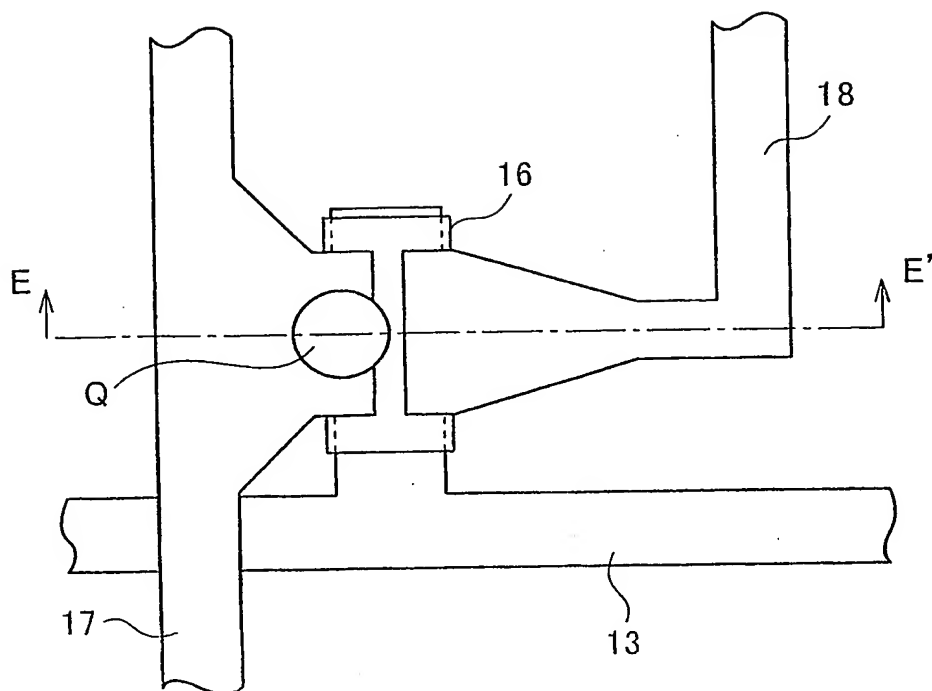


FIG. 13



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FIG. 14 (a)

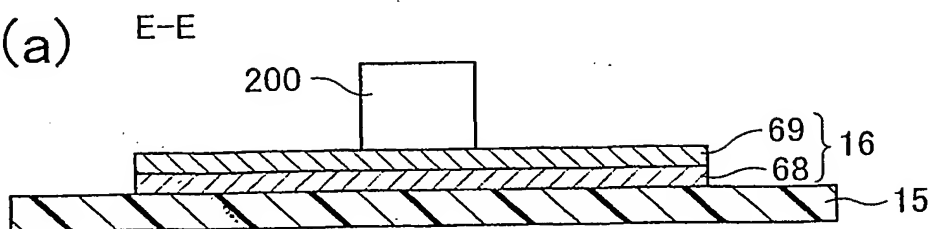


FIG. 14 (b)

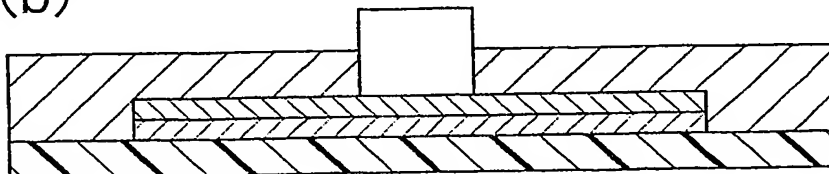


FIG. 14 (c)

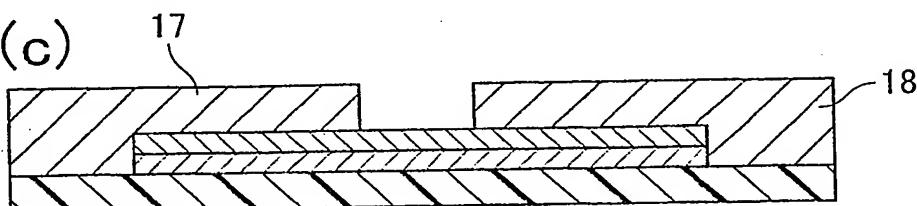


FIG. 14 (d)

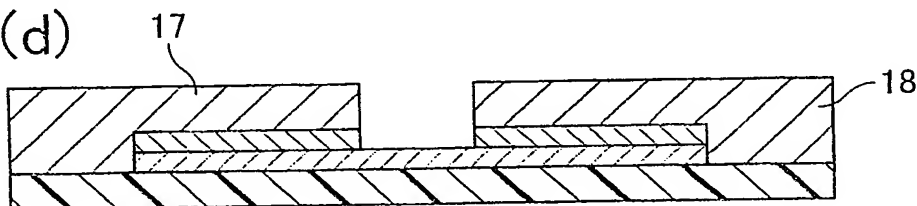


FIG. 14 (e)

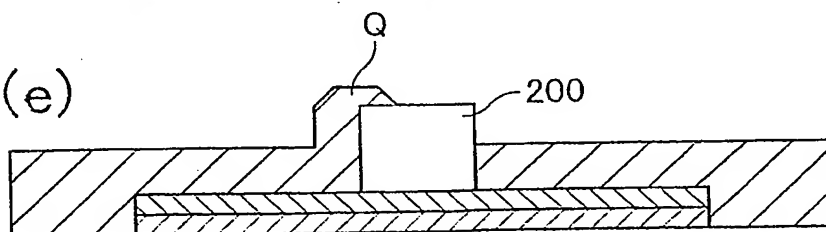


FIG. 14 (f)

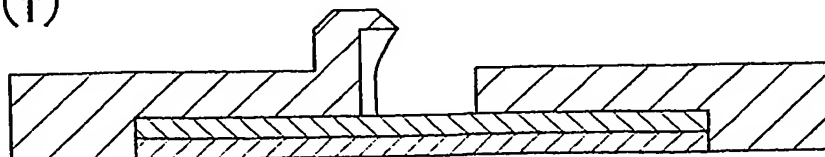


FIG. 14 (g)

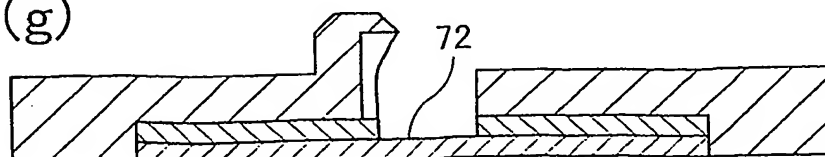


FIG. 15

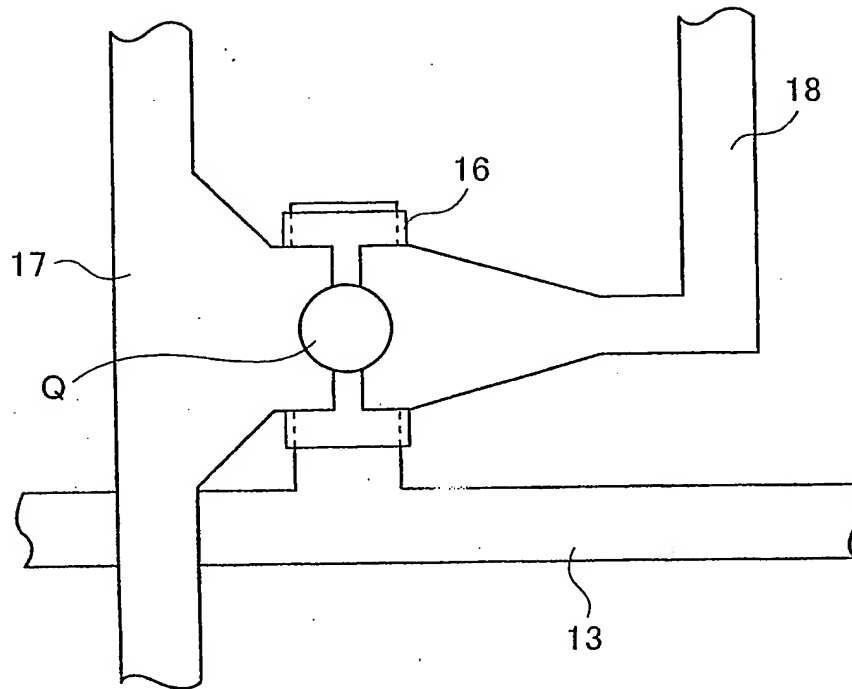


FIG. 16 (a)

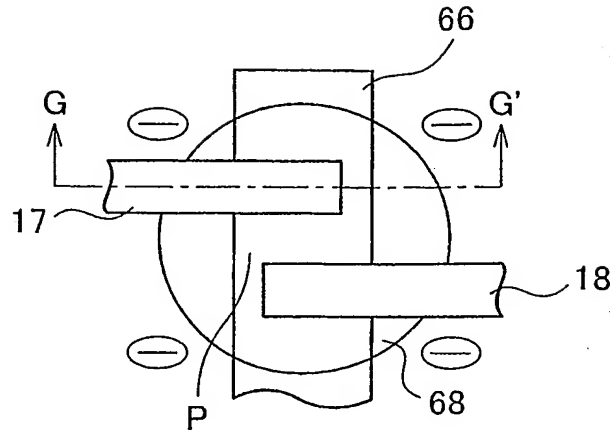


FIG. 16 (b)

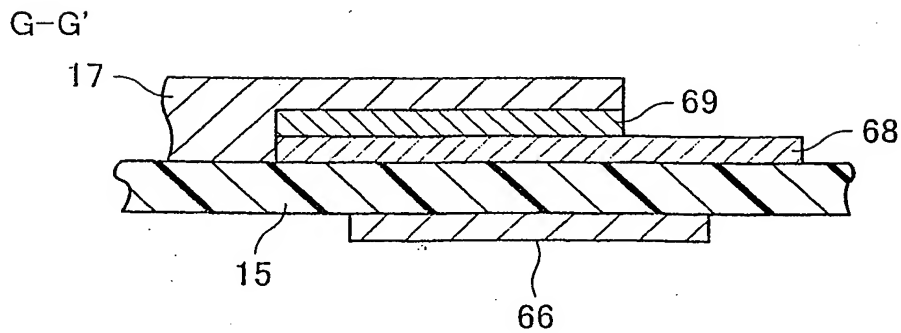


FIG. 17 (a)

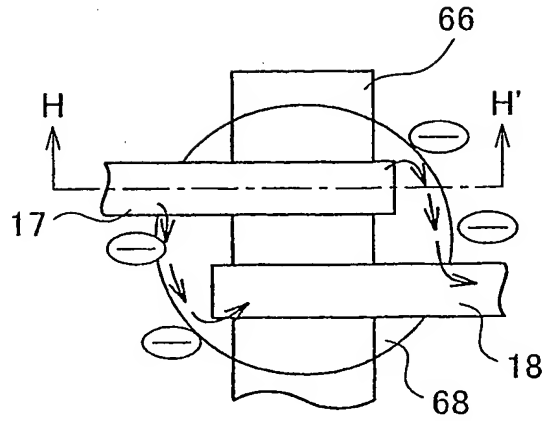


FIG. 17 (b)

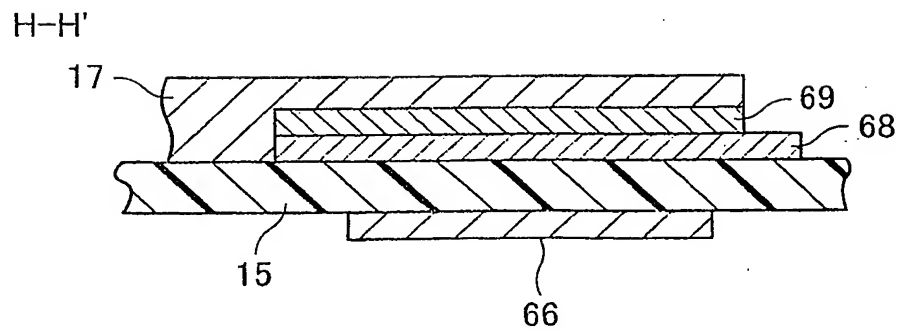




FIG. 18

